









CES2322

20V Δ 17mΩ Δ 6.2A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

SOT23 package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)}

Rugged and reliable

MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	20V
Gate-Source Voltage	V _{GS}	±10V
Continuous Drain Current at T _A = 25°C	I _D	6.2A
Continuous Drain Current at T _A = 70°C	I _D	5A
Pulsed Drain Current Note 1	I _{DM}	24.8A
Maximum Power Dissipation	P _D	1.25W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

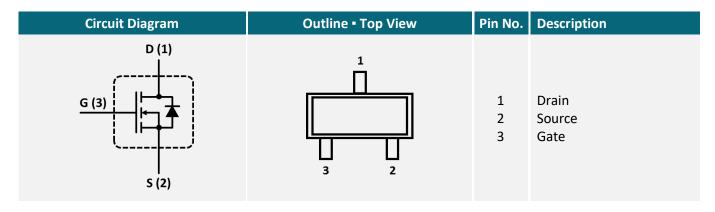
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	100°C/W

APPLICATIONS

Battery	DC	Load	Power	USB
Pack	Fan	Switches	Banks	Storage
+4-			4	P

PIN DESCRIPTION



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ELECTRICAL CHARACTERISTICS ▲ T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_{DSS}	20			V
Zero Gate Voltage Drain Current	$V_{DS} = 20V$, $V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 10V$, $V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -10V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	0.4		1	V
Static Drain-Source On-Resistance	$V_{GS} = 4.5V, I_D = 6A$	R _{DS(ON)}		17	22	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 2.5V, I_D = 5.2A$	R _{DS(ON)}		21	30	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$	C _{ISS}		510		pF
Output Capacitance	V_{DS} = 16V, V_{GS} = 0V, f = 1MHz C_{OSS}			110		pF
Reverse Transfer Capacitance	$V_{DS} = 16V$, $V_{GS} = 0V$, $f = 1MHz$ C_{RSS}					pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{DD} = 16V$, $V_{GS} = 4.5V$, $I_D = 3A$, $R_{G(ext)} = 6\Omega$	t _{D(ON)}		8		ns
Turn-On Rise Time	V_{DD} = 16V, V_{GS} = 4.5V, I_D = 3A, $R_{G(ext)}$ = 6Ω	t_{R}		9		ns
Turn-Off Delay Time	V_{DD} = 16V, V_{GS} = 4.5V, I_D = 3A, $R_{G(ext)}$ = 6Ω	$t_{D(OFF)}$		35		ns
Turn-Off Fall Time	V_{DD} = 16V, V_{GS} = 4.5V, I_D = 3A, $R_{G(ext)}$ = 6Ω	t _F		9		ns
Total Gate Charge	$V_{DS} = 16V$, $V_{GS} = 4.5V$, $I_D = 3A$	Q_{G}		10		nC
Gate Source Charge	$V_{DS} = 16V$, $V_{GS} = 4.5V$, $I_D = 3A$	Q_{GS}		0.5		nC
Gate Drain Charge	$V_{DS} = 16V$, $V_{GS} = 4.5V$, $I_{D} = 3A$	Q_{GD}		4		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		I _S			1	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$, $I_S = 1A$	V_{SD}			1	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

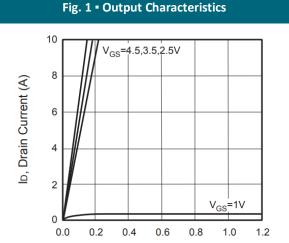


Fig. 2 • Transfer Characteristics

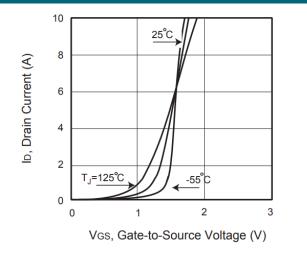


Fig. 3 • Capacitance

VDS, Drain-to-Source Voltage (V)

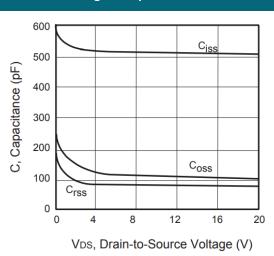


Fig. 4 • On-Resistance Variation with Temperature

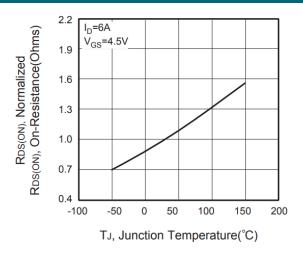


Fig. 5 • Gate Threshold Variation with Temperature

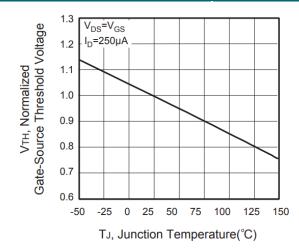
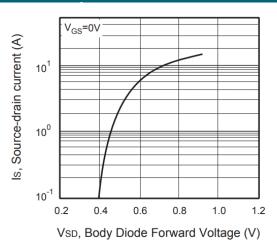


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



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Fig. 7 • Gate Charge

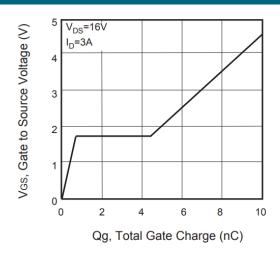


Fig. 8 • Maximum Safe Operating Area

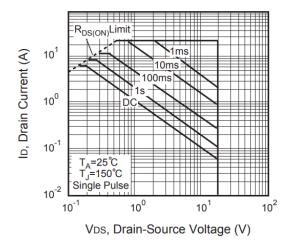
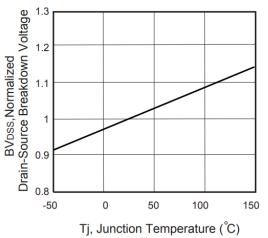


Fig. 9 • Breakdown Voltage Variation vs. Temperature



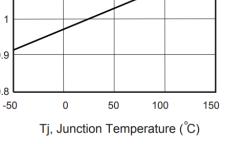


Fig. 10 • Switching Test Circuit

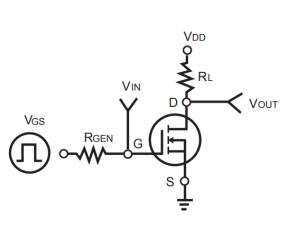
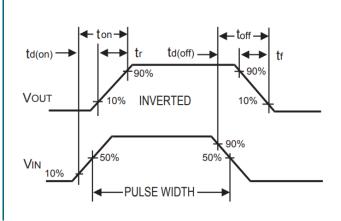


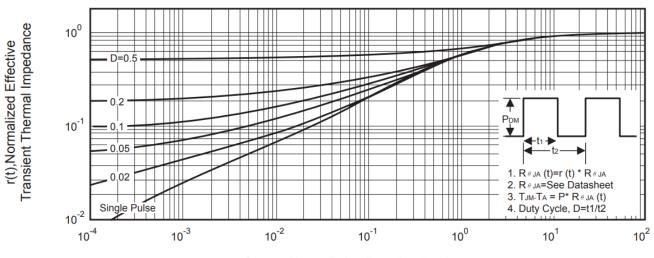
Fig. 11 • Switching Waveforms





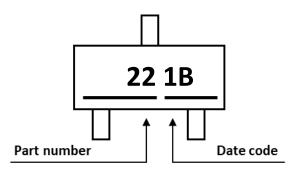
REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



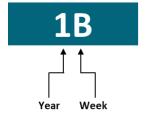
Square Wave Pulse Duration (sec)

PART MARKING

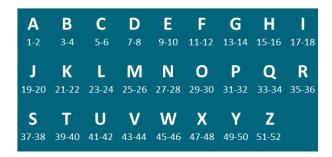


DATE CODE

Example: 1B



Coding list for "Week"

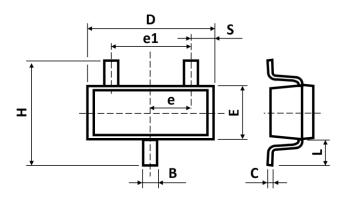


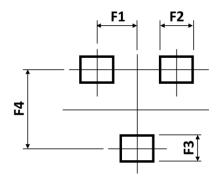
Coding list for "Year"

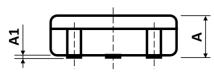




PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.890	-	1.250
A1	0.000	-	0.100
В	0.300	-	0.500
С	0.085	-	0.200
D	2.720	-	3.040
E	1.400	-	1.800

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
е		0.95 BSC				
e1	1.780	-	2.180			
Н	2.500	-	3.100			
L	0.550 REF					
S	0.410	-	0.610			

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	0.950	-	
F2	-	0.760	-	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F3	-	0.760	-
F4	-	2.290	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

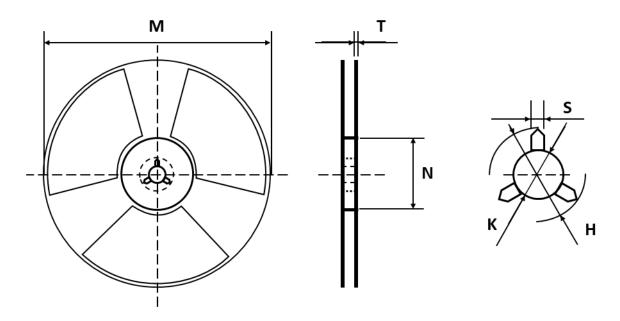
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	
CES2322	SOT23	7" Reel	3,000pcs	15,000pcs	

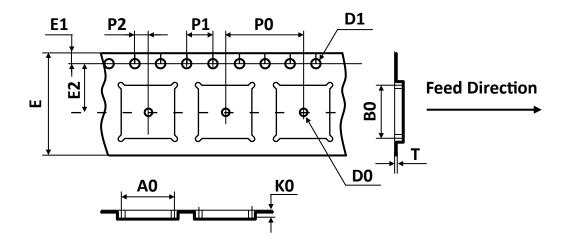


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	K	S
8mm	Ø180	Ø178.00	Ø54.00	1.20	20.00	13.30	3.00
	9100	±1.00	±0.50	±0.20	±1.00	±0.30	±1.00

TAPE DIMENSIONS ▲ All dimensions in mm

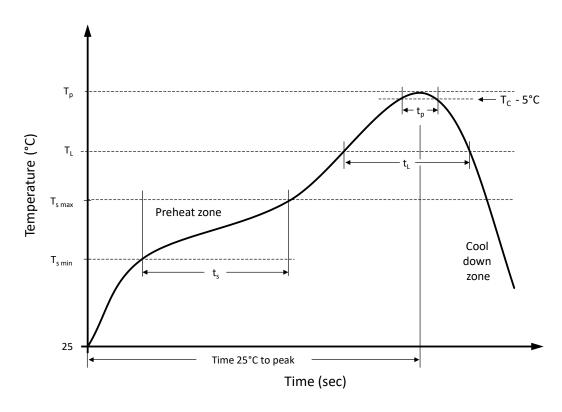


Package	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
SOT23	3.25	3.25	1.35	1.00	1.50	8.00	1.75	3.50	4.00	4.00	2.00	0.20
30123	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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